



US 20230231537A1

(19) **United States**  
(12) **Patent Application Publication** (10) **Pub. No.: US 2023/0231537 A1**  
Hou et al. (43) **Pub. Date: Jul. 20, 2023**

(54) **RESONATOR AND MANUFACTURING METHOD THEREOF, FILTER, AND ELECTRONIC DEVICE**

*H03H 9/56* (2006.01)

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(52) **U.S. Cl.**  
CPC ..... *H03H 9/175* (2013.01); *H03H 3/02*  
(2013.01); *H03H 9/564* (2013.01); *H03H*  
*9/568* (2013.01); *H03H 2003/025* (2013.01)

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(57) **ABSTRACT**

(21) Appl. No.: **18/187,846**

(22) Filed: **Mar. 22, 2023**

**Related U.S. Application Data**

(63) Continuation of application No. PCT/CN2020/  
117230, filed on Sep. 23, 2020.

**Publication Classification**

(51) **Int. Cl.**  
*H03H 9/17* (2006.01)  
*H03H 3/02* (2006.01)

Disclosed are a resonator and a manufacturing method thereof, a filter, and an electronic device. The resonator includes a substrate, a Bragg reflection layer, and a piezoelectric layer that are sequentially stacked. A first electrode is disposed on a surface that is of the piezoelectric layer and that faces the Bragg reflection layer, a second electrode is disposed on a surface that is of the piezoelectric layer and that is away from the Bragg reflection layer, a border ring is disposed on a surface that is of the second electrode and that is away from the piezoelectric layer, and the resonator has a first resonance region and a second resonance region corresponding to the border ring.

